VS-HFA12PA120C-N3

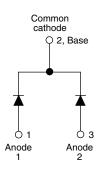
Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 2 x 6 A



www.vishay.com





PRIMARY CHARACTERISTICS								
I _{F(AV)}	2 x 6 A							
V _R	1200 V							
V _F at I _F	2.4 V							
t _{rr} typ.	26 ns							
T _J max.	150 °C							
Package	TO-247AC 3L							
Circuit configuration	Common cathode							

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC[®]-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA12PA120C... is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. The VS-HFA12PA120C... has basic ratings of 1200 V and 6 A per leg continuous current. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA12PA120C... is ideally suited for applications in power supplies and power conversion systems (such as inverters, converters, UPS systems, and power factor correction circuits), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Cathode to anode voltage	V _R		1200	V				
Maximum continuous forward current		T _C = 100 °C	6					
per device	IF	$1_{\rm C} = 100$ C	12	А				
Single pulse forward current	I _{FSM}	t _p = 10 ms	80	A				
Maximum repetitive forward current	I _{FRM}		24					
Maximum neuror discinction	Р	T _C = 25 °C	62.5	W				
Maximum power dissipation	P _D	T _C = 100 °C	25	vv				
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C				

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Document Number: 94597

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COMPLIANT HALOGEN

VS-HFA12PA120C-N3



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ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	1200	-	-				
Maximum forward voltage		I _F = 6 A	-	2.7	3.0	V			
	V _{FM}	I _F = 12 A	-	3.5	3.9				
		I _F = 6 A, T _J = 125 °C	-	2.4	2.8				
Maximum reverse		$V_{R} = V_{R}$ rated	-	0.26	5.0				
leakage current	I _{RM}	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$ - 110		110	500	μA			
Junction capacitance	CT	V _R = 200 V	-	9.0	14	pF			
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH			

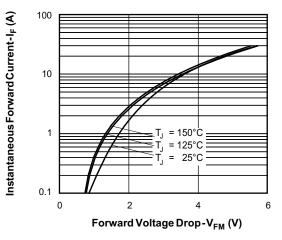
DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$	A/ μ s, V _R = 30 V	-	26	-			
Reverse recovery time	t _{rr1}	T _J = 25 °C		-	53	80	ns		
	t _{rr2}	T _J = 125 °C		-	87	130			
Peak recovery current	I _{RRM1}	T _J = 25 °C	I _F = 6 A	-	4.4	8.0	A		
	I _{RRM2}	T _J = 125 °C		-	5.0	9.0			
	Q _{rr1}	T _J = 25 °C	dI _F /dt = 200 A/µs V _B = 200 V	-	116	320			
Reverse recovery charge	Q _{rr2}	T _J = 125 °C	V _R = 200 V	-	233	585	no		
Peak rate of fall of recovery	dl _{(rec)M} /dt1	T _J = 25 °C		-	180	-	A/µs		
current during t _b	dl _{(rec)M} /dt2	T _J = 125 °C		-	100	-	rvµs		

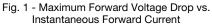
THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Thermal resistance, junction to case	R _{thJC}		-	-	2.0					
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	K/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.50	-					
Weight			-	2.0	-	g				
weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-247AC 3L		HFA12	PA120C					



VS-HFA12PA120C-N3

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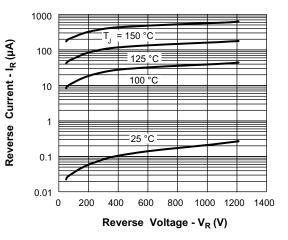


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

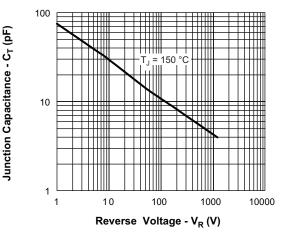


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

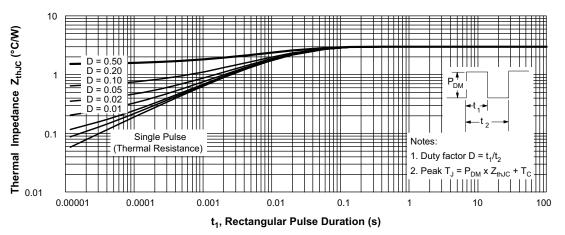


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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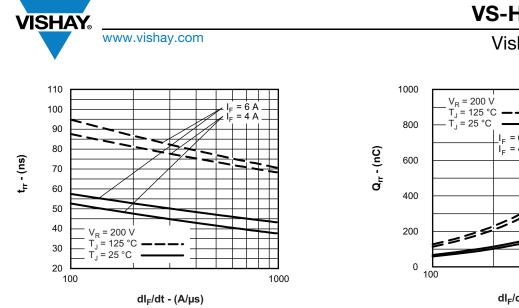


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

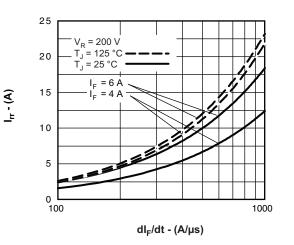


Fig. 6 - Typical Recovery Current vs. dl_F/dt

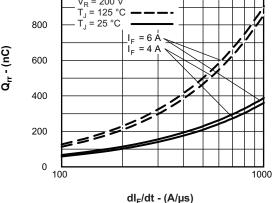


Fig. 7 - Typical Stored Charge vs. dl_F/dt

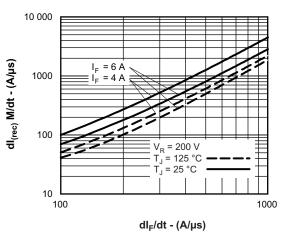


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

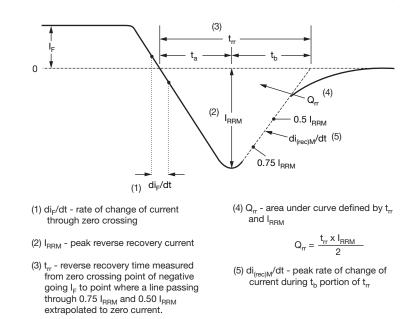


Fig. 9 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code	VS-	HF	Α	12	PA	120	С	-N3
		2	3	4	5	6	7	8
	1 -			niconduc	ctors pro	oduct		
	2 -		KFRED [®]	-				
	4 -			ng (12 =	= 12 A)			
	5 -	PA	= TO-24	47AC, 3	pins			
	6 -	Vol	age rati	ng: (120) = 1200) V)		
	7 -			iguratior				
	8			ntal digit		oomolic	nt and	totolly
		-193	– nalog	gen-free	, KUHS-	complia	ini, and	locally

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	PACKAGING DESCRIPTION						
VS-HFA12PA120C-N3	25	500	Antistatic plastic tube					

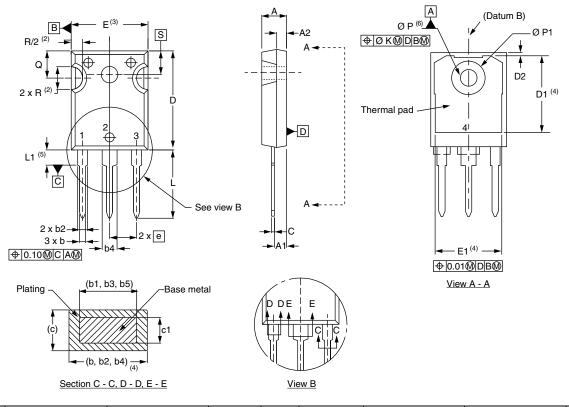
LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96138					
Part marking information	www.vishay.com/doc?95007					



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TO-247AC 3L

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES	
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWDOL	MIN.	MAX.	MIN.	MAX.	NOTES
A	4.65	5.31	0.183	0.209			D2	0.51	1.35	0.020	0.053	
A1	2.21	2.59	0.087	0.102			E	15.29	15.87	0.602	0.625	3
A2	1.17	1.37	0.046	0.054			E1	13.46	-	0.53	-	
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	5 BSC	
b1	0.99	1.35	0.039	0.053			ØК	0.2	254	0.0)10	
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634	
b3	1.65	2.34	0.065	0.092			L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135			ØΡ	3.56	3.66	0.14	0.144	
b5	2.59	3.38	0.102	0.133			Ø P1	-	7.39	-	0.291	
С	0.38	0.89	0.015	0.035			Q	5.31	5.69	0.209	0.224	
c1	0.38	0.84	0.015	0.033			R	4.52	5.49	0.178	0.216	
D	19.71	20.70	0.776	0.815	3		S	5.51	BSC	0.217	' BSC	
D1	13.08	-	0.515	-	4							

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

(4) Thermal pad contour optional with dimensions D1 and E1

⁽⁵⁾ Lead finish uncontrolled in L1

⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-247 with exception of dimension Q

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